MOSFETs Silicon Carbide N-Channel MOS

TW060N120C

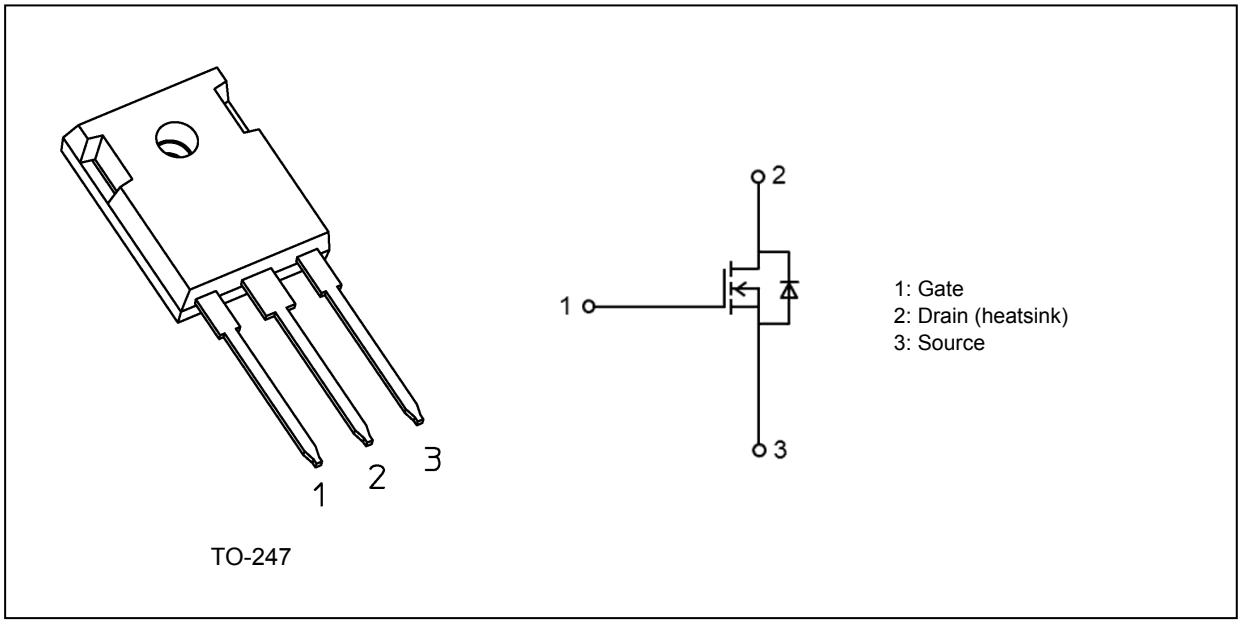
1. Applications

- Switching Voltage Regulators

2. Features

(1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
(2) Low diode forward voltage: V_{DSF} = -1.35 V (typ.)
(3) High voltage: V_{DSS} = 1200 V
(4) Low drain-source on-resistance: $R_{DS(ON)}$ = 60 mΩ (typ.)
(5) Less susceptible to malfunction due to high threshold voltage: V_{th} = 3.0 to 5.0 V (V_{DS} = 10 V, I_D = 4.2 mA)
(6) Recommended gate - source drive voltage: V_{GS_on} = 18 V, V_{GS_off} = 0 V
(7) Enhancement mode.

3. Packaging and Internal Circuit



Start of commercial production
2022-07

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4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	1200	V
Gate-source voltage		V_{GSS}	+25/-10	
Drain current (DC)	(T_c = 25 °C)	I_D	36	A
Drain current (DC)	(T_c = 100°C)	I_D	26	
Drain current (pulsed)	(T_c = 25 °C)	I_{DP}	87	
Drain current (pulsed)	(T_c = 100°C)	I_{DP}	65	
Power dissipation	(T_c = 25°C)	P_D	170	W
Channel temperature		T_{ch}	175	°C
Storage temperature		T_{stg}	-55 to 175	
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	0.879	°C/W
Channel-to-ambient thermal resistance	$R_{th(ch-a)}$	50	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.
It should be used for switching applications.

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6. Electrical Characteristics

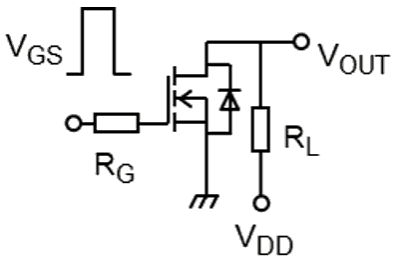
6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = +25/-10 V, V_{DS} = 0 V	—	—	±0.1	μA
Drain cut-off current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V	—	0.7	10	
		T_a = 150 °C, V_{DS} = 1200 V, V_{GS} = 0 V	—	4	—	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = 4 mA, V_{GS} = 0 V	1200	—	—	V
Gate threshold voltage (Note 2)	V_{th}	V_{DS} = 10 V, I_D = 4.2 mA	3.0	—	5.0	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = 18 V, I_D = 18 A	—	60	78	mΩ
		T_a = 150 °C, V_{GS} = 18 V, I_D = 18 A	—	82	—	

Note 2: Please be sure to apply I_{GSS} (V_{GS} = 25 V) before the V_{th} test.

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = 0 V, f = 100 kHz	—	1530	—	pF
Reverse transfer capacitance	C_{rss}		—	2.8	—	
Output capacitance	C_{oss}		—	82	—	
Effective output capacitance (energy related)	$C_{o(er)}$		—	97	—	
Effective output capacitance (time related)	$C_{o(tr)}$		—	146	—	
Output charge	Q_{oss}		—	117	—	nC
C_{oss} stored energy	E_{oss}		—	31	—	μJ
Gate resistance	r_g	V_{DS} = OPEN, f = 1 MHz	—	3.2	—	Ω
Switching time (rise time)	t_r	See Fig. 6.2.1	—	40	—	ns
Switching time (turn-on time)	t_{on}		—	68	—	
Switching time (fall time)	t_f		—	33	—	
Switching time (turn-off time)	t_{off}		—	71	—	ns



V_{DD} ≈ 800 V
V_{GS} = 0 V / 18 V
I_D = 18 A
R_L = 44 Ω
R_G = 4.7 Ω
Duty ≤ 1 %, t_w = 1 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ 800 V, V_{GS} = 18 V, I_D = 18 A	—	46	—	nC
Gate-source charge 1	Q_{gs1}		—	18	—	
Gate-drain charge	Q_{gd}		—	7.8	—	

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6.4. Source · Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 3)	I_{DR}	T_c = 25 °C, V_{GS} = -5 V	—	—	30	A
		T_c = 100 °C, V_{GS} = -5 V	—	—	20	
		T_c = 25 °C, V_{GS} = 18 V	—	—	36	
		T_c = 100 °C, V_{GS} = 18 V	—	—	26	
Reverse drain current (pulsed) (Note 3)	I_{DRP}	T_c = 25 °C, V_{GS} = -5 V	—	—	87	
		T_c = 100 °C, V_{GS} = -5 V	—	—	33	
		T_c = 25 °C, V_{GS} = 18 V	—	—	87	
		T_c = 100 °C, V_{GS} = 18 V	—	—	65	
Diode forward voltage	V_{DSF}	I_{DR} = 8 A, V_{GS} = -5 V	—	-1.35	-1.80	V
		T_a = 150 °C, I_{DR} = 8 A, V_{GS} = -5 V	—	-1.70	—	
Reverse recovery time	t_{rr}	I_{DR} = 12 A, V_{GS} = 0 V, V_{DD} = 800 V, -dI_{DR}/dt = 1000 A/μs	—	54	—	ns
Reverse recovery charge	Q_{rr}		—	259	—	nC
Peak reverse recovery current	I_{rr}		—	9.6	—	A

Note 3: Ensure that the channel temperature does not exceed 175 °C.

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7. Marking (Note)

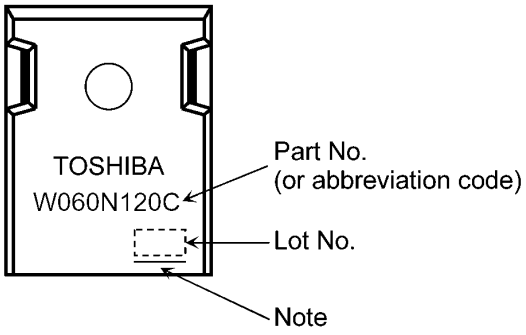


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.
Not underlined: [[Pb]]/INCLUDES > MCV
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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8. Characteristics Curves (Note)

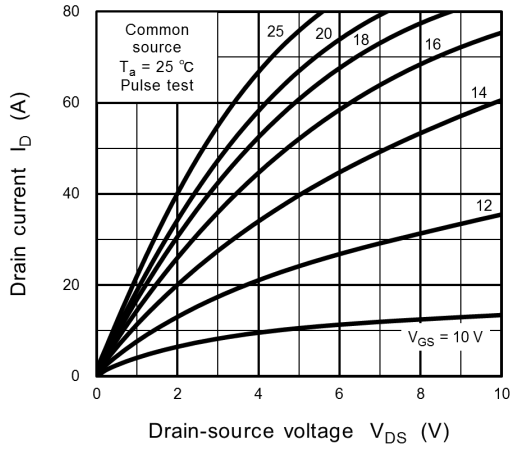


Fig. 8.1 I_D - V_{DS}

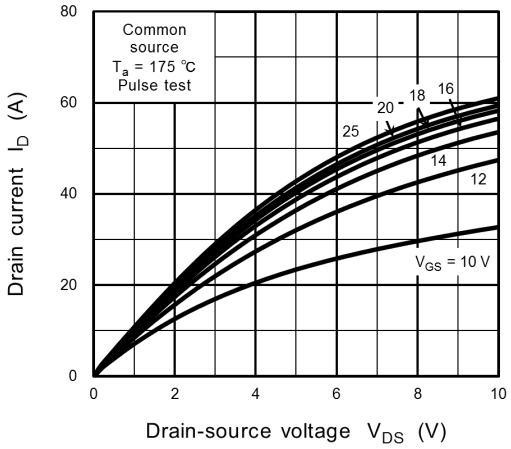


Fig. 8.2 I_D - V_{DS}

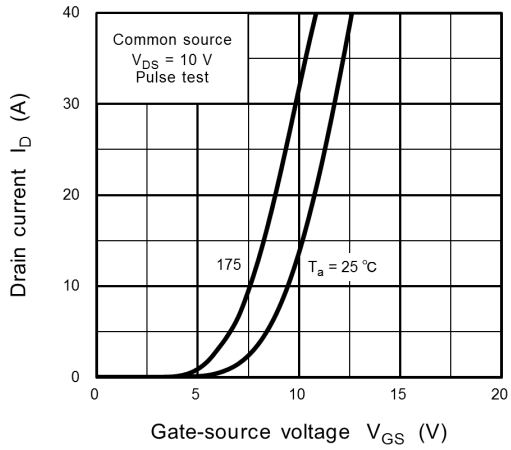


Fig. 8.3 I_D - V_{GS}

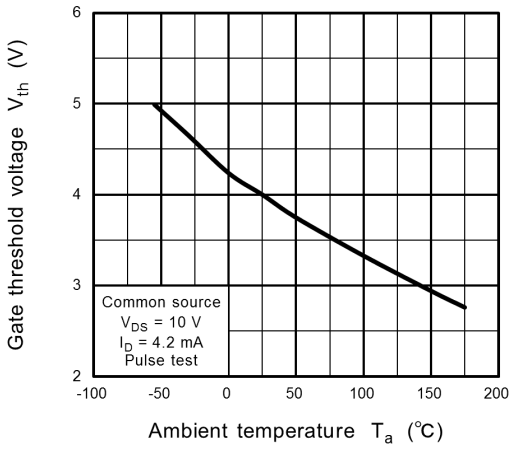


Fig. 8.4 V_{th} - T_a

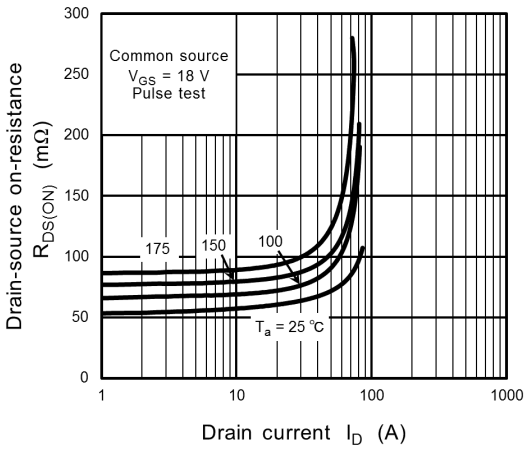


Fig. 8.5 $R_{DS(ON)}$ - I_D

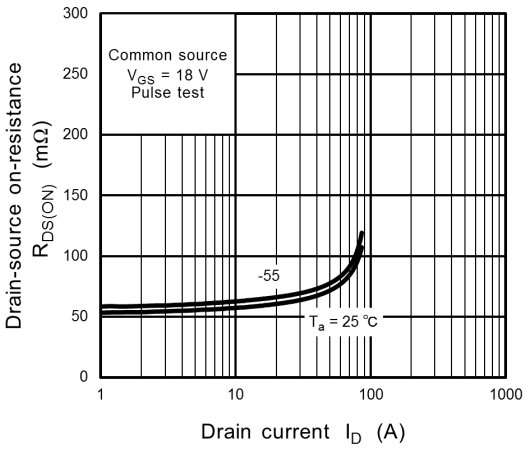


Fig. 8.6 $R_{DS(ON)}$ - I_D

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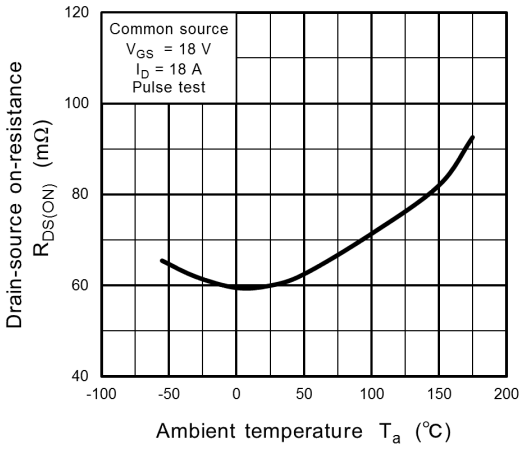


Fig. 8.7 $R_{DS(ON)}$ - T_a

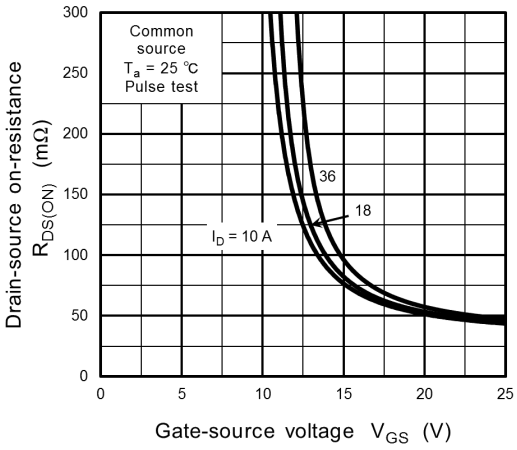


Fig. 8.8 $R_{DS(ON)}$ - V_{GS}

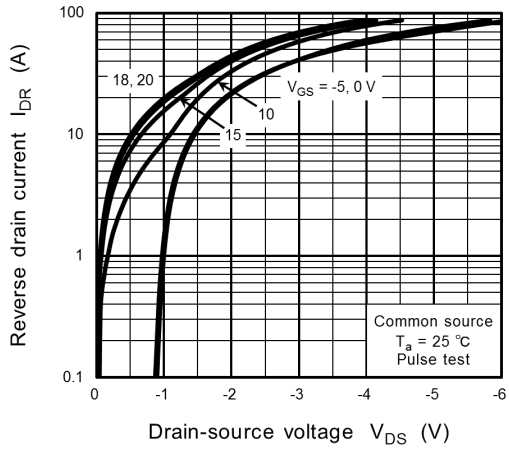


Fig. 8.9 I_{DR} - V_{DS}

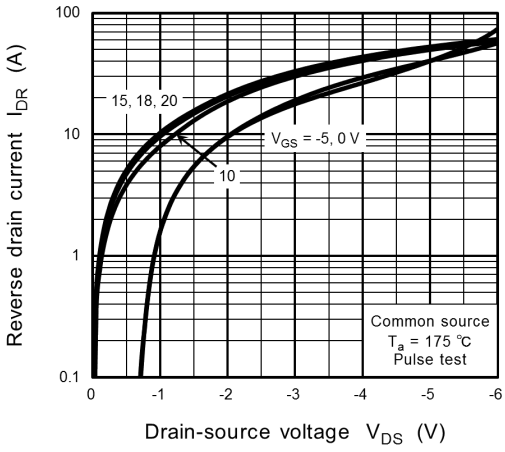


Fig. 8.10 I_{DR} - V_{DS}

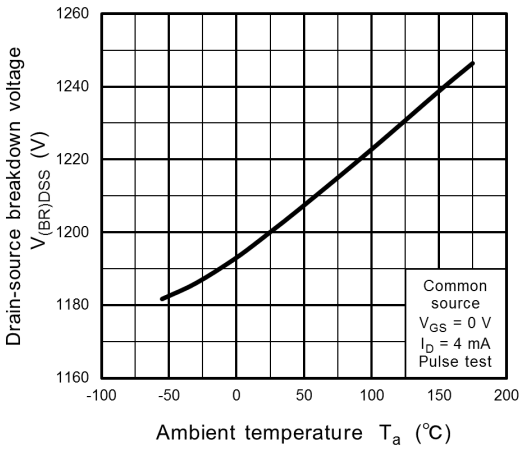


Fig. 8.11 V_{DSS} - T_a

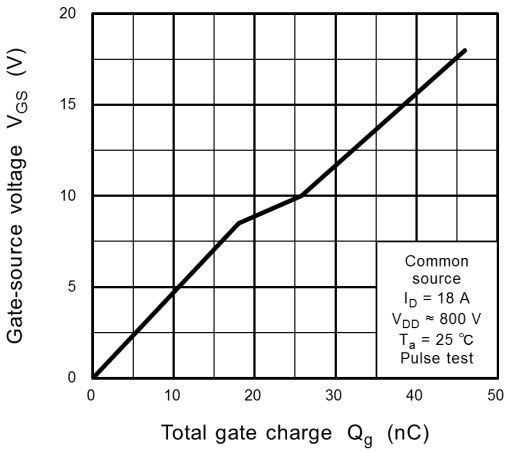


Fig. 8.12 Dynamic Input Characteristics

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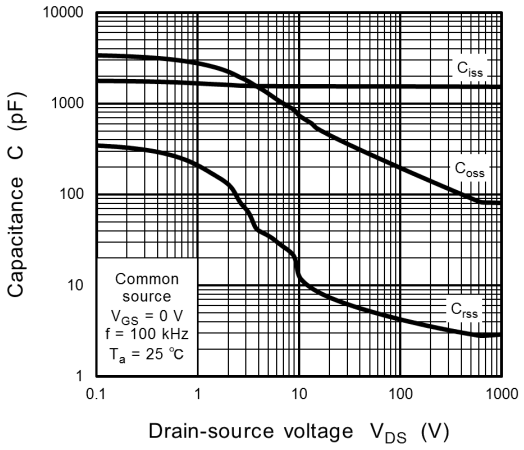


Fig. 8.13 C - V_{DS}

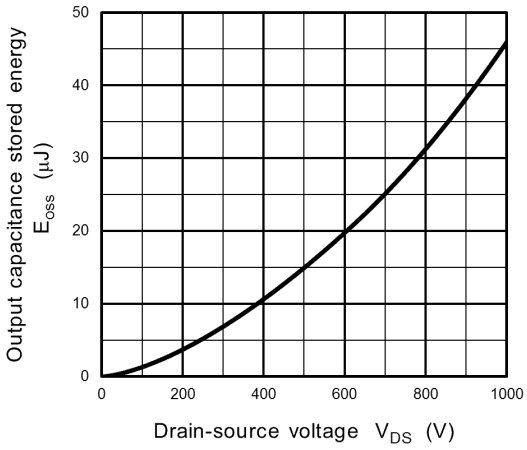


Fig. 8.14 E_{oss} - V_{DS}

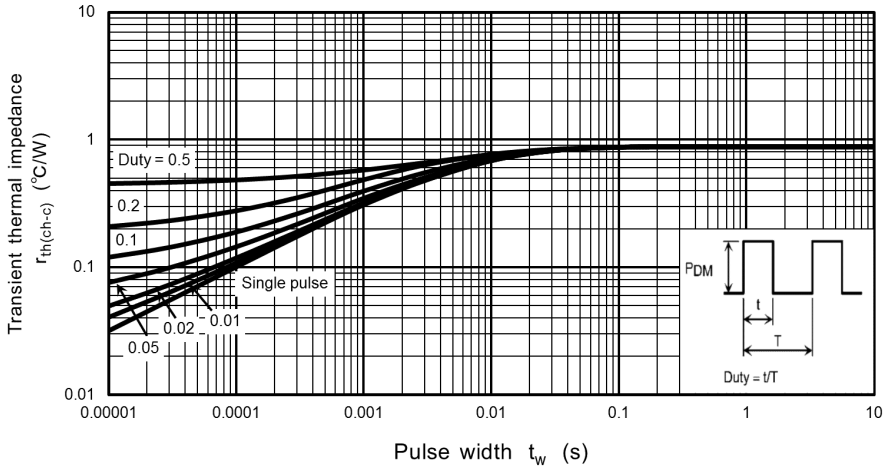


Fig. 8.15 $r_{th(ch-c)}$ - t_w
(Guaranteed Maximum)

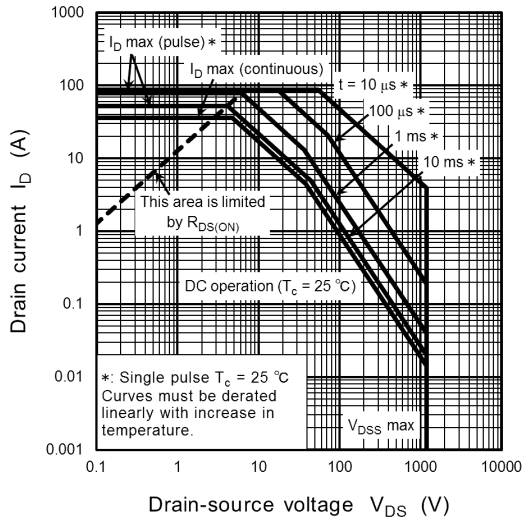


Fig. 8.16 Safe Operating Area
(Guaranteed Maximum)

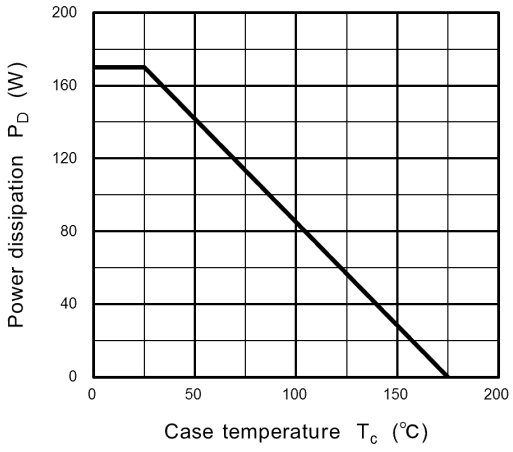


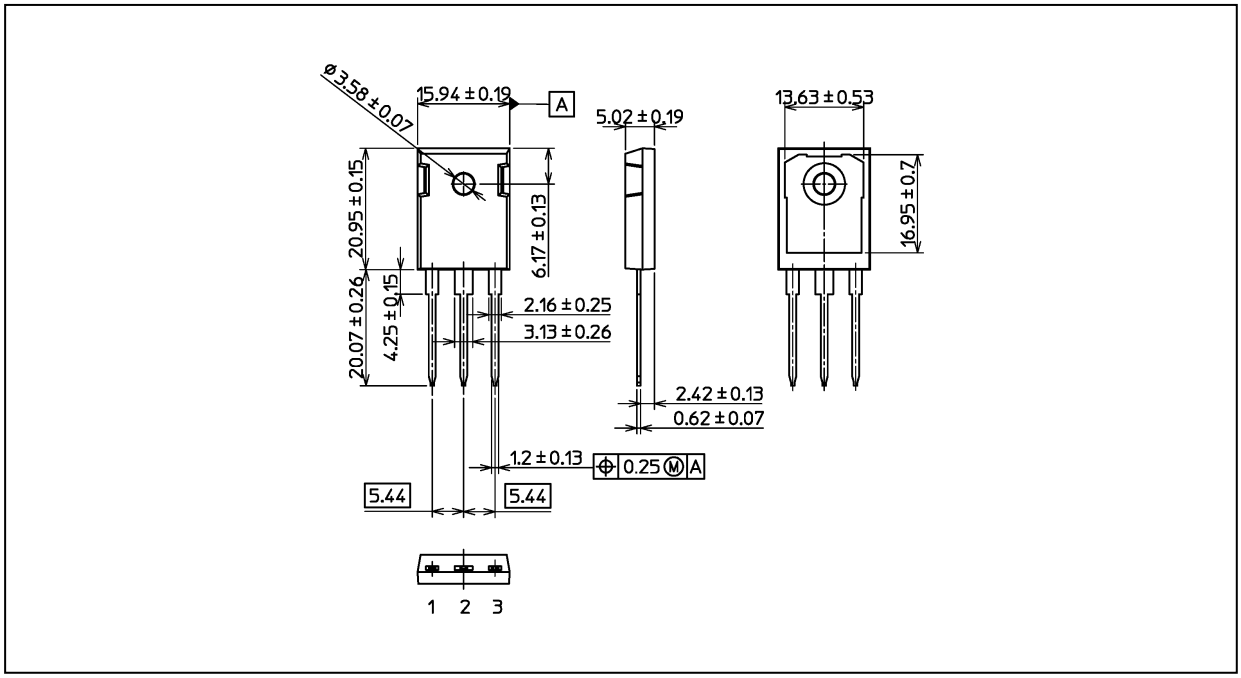
Fig. 8.17 P_D - T_c
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

Package Name(s)
TOSHIBA: 2-16L1A
Nickname: TO-247

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